Panasonic 1 ICP SiN\textsubscript{x} etching CF4 O\textsubscript{2}

Data provided by Jon Barton

- For in-house PECVD Oxide. LPCVD oxide from outside will have lower rates.
- ICP 500W
- Bias Power varies
- Pressure Varied
- 50 sccm CF4
- 5 sccm O\textsubscript{2}
- Very fast etch rates
- About 1:1 etch ratio with PR
Slowing down the rate

- For in-house PECVD Oxide. LPCVD oxide from outside will have lower rates.
- ICP Varied
- Bias Power 25W
- 50 sccm CF4
- 5 sccm O2
- 1 Pa pressure